



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D T _C = +25°C	
60V	$4.4m\Omega$ @ $V_{GS} = 10V$	100A	
007	$6.4 \text{m}\Omega$ @ V _{GS} = 4.5V	85A	

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
 - Low RDS(ON) Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- High Frequency Switching
- Synchronous Rectification
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

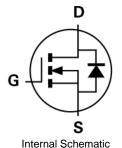


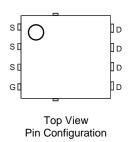




Top View Bottom View

PowerDI5060-8 (SWP) (Standard)





Ordering Information (Note 4)

Part Number	Case	Packaging
DMT64M2LPSW-13	PowerDI5060-8 (SWP) (Standard)	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking T64M2LSW = Product Type Marking Code YYWW or YYWW= Date Code Marking YY or YY = Year (ex: 20 = 2020) WW = Week (01 to 53)

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		lD	20.7 16.6	А	
Continuous Drain Current (Note 6) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		ΙD	100 82	А	
Maximum Continuous Body Diode Forward Current (Note 6)			Is	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			IDM	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	400	Α
Avalanche Current, L = 1mH			las	18.2	Α
Avalanche Energy, L = 1mH			Eas	165.6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{ÐJA}	44	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	83.3	W
Thermal Resistance, Junction to Case (Note 6)		R _{eJC}	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

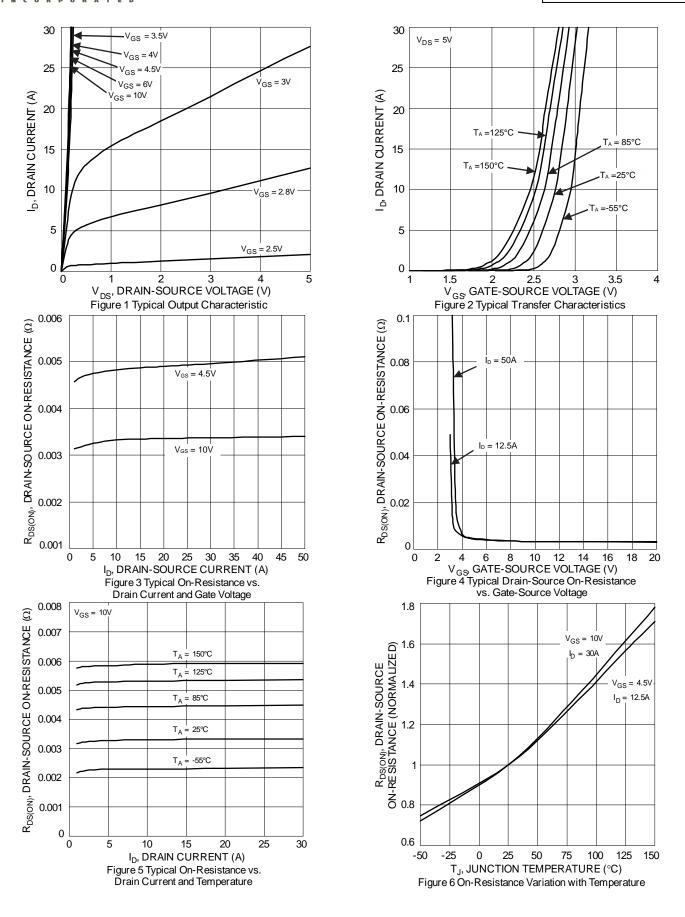
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1.2	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descent	_	3.3	4.4	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Dialii-Source Off-Resistance	Rds(on)	_	4.7	6.4	11177	V _G S = 4.5V, I _D = 12.5A	
Diode Forward Voltage	VsD	_	0.8	1.2	V	V _G S = 0V, I _S = 50A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	2799	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	950	_	pF		
Reverse Transfer Capacitance	Crss	_	79	_			
Gate Resistance	Rg	_	0.63	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	46.7	_		V _{DD} = 30V, I _D = 50A	
Total Gate Charge (VGS = 4.5V)	Q _G	_	24.1	_	nC		
Gate-Source Charge	Qgs	_	8.2	_	IIC		
Gate-Drain Charge	Q _{GD}	_	11.0	_			
Turn-On Delay Time	t _{D(ON)}	_	6.5	_		$V_{DD} = 30V$, $V_{GS} = 10V$, $I_{D} = 30A$, $R_{G} = 3.3\Omega$	
Turn-On Rise Time	t _R	_	6.9	_			
Turn-Off Delay Time	tD(OFF)	_	26.1	_	ns		
Turn-Off Fall Time	t _F	_	11.2	_			
Body Diode Reverse Recovery Time	trr	_	40.1	_	ns	I- 20A di/dt 400A/v-	
Body Diode Reverse Recovery Charge	Q _{RR}	_	51.1	_	nC	I _F = 30A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:

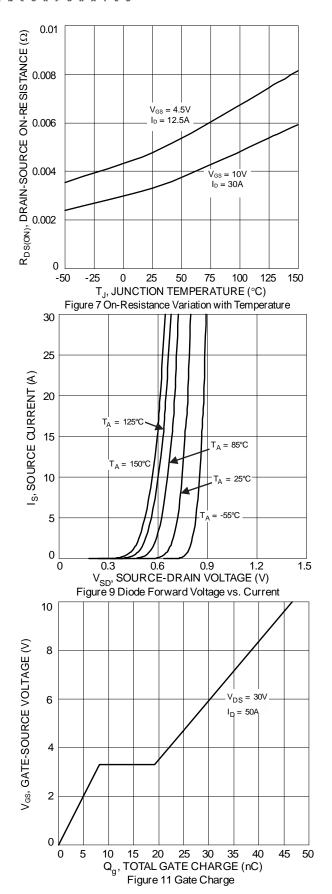
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

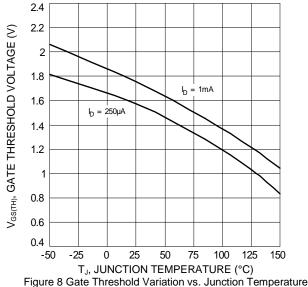
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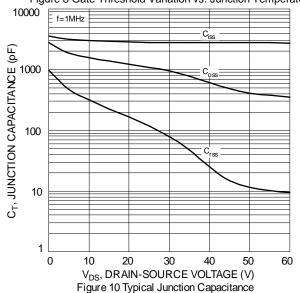


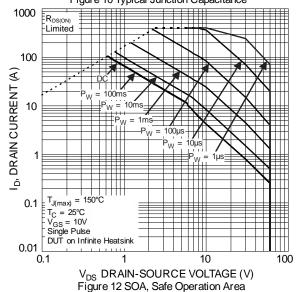




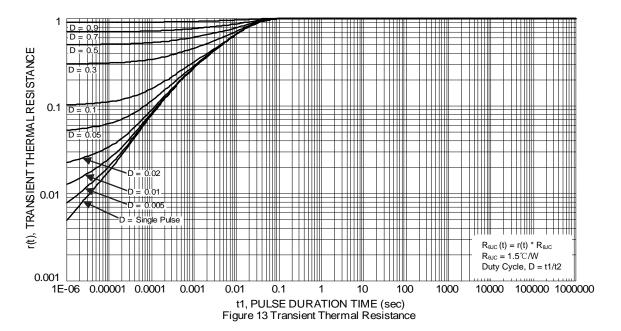










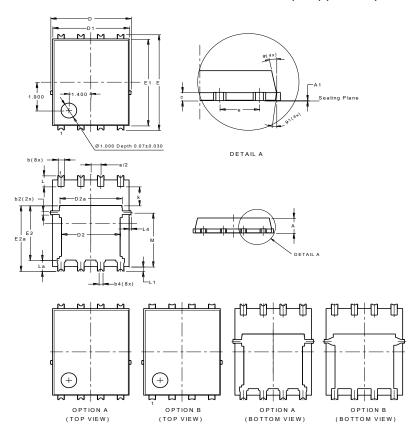




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Standard)

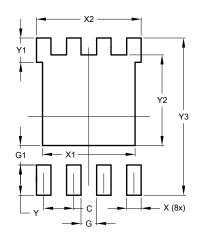


PowerDI5060-8 (SWP)					
(Standard) ´					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	-		
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS0)		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
Е	6	.40 BS0)		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195 4.595		4.395		
е	1	.27BSC)		
k	1.05		-		
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Standard)



Dimensions	Value		
Dimensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		

Value



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DMT64M2LPSW 7 of 7

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